

Midterm III

Information that will be provided with the exam

Permittivity of free space $\epsilon_0 = 8.85 \times 10^{-14} \text{ F/cm} = 8.85 \times 10^{-12} \text{ F/m}$

Element of charge $q = 1.6 \times 10^{-19} \text{ C}$

1 Coulomb is equivalent to 6.25×10^{18} charges.

Charge on an electron is $-q$

Relative permittivity (or relative dielectric constant) values for Si, SiO₂

Avagadro's number: 6.02×10^{23}

Statement that if an element has an atomic weight of A, then A grams of that element will have 6.02×10^{23} atoms.

Saturation velocity for electrons in silicon: 10^7 cm/s

n_i (intrinsic carrier concentration in silicon at 300 K) = 10^{10} cm^{-3}

Conductivity (σ) and Drift Current Density (J) for electrons in Semiconductor:

$\sigma = qn\mu_n$ where n is the volume carrier density and μ_n is the electron mobility. Similar expression for holes with p (volume hole concentration) instead of n and hole mobility μ_p instead of μ_n

$\mathbf{J} = \sigma \mathbf{E}$, where \mathbf{E} is the electric field

Parallel Plate Capacitor:

Capacitance per unit area = $\frac{\epsilon_0 \epsilon_r}{t_{ox}}$ where t_{ox} is the dielectric thickness

MOSFET Linear Region:

NMOS: When $V_{DS} \leq V_{GS} - V_T$

$$I_D = \mu_n C_{ox} \frac{W}{L} \left([V_{GS} - V_t] V_{DS} - \frac{v_{DS}^2}{2} \right)$$

PMOS: When $|V_{DS}| \leq |V_{GS}| - |V_T|$

$$I_D = \mu_p C_{ox} \frac{W}{L} \left([V_{GS} - V_t] V_{DS} - \frac{v_{DS}^2}{2} \right)$$

Saturation Region:

NMOS: When $V_{DS} > V_{GS} - V_T$

$$I_D = \frac{1}{2} (\mu_n C_{ox}) \left(\frac{W}{L} \right) (V_{GS} - V_t)^2$$

PMOS: When $|V_{DS}| > |V_{GS}| - |V_T|$

$$I_D = \frac{1}{2} (\mu_p C_{ox}) \left(\frac{W}{L} \right) (V_{GS} - V_t)^2$$

Small signal model parameters:

$$\text{Small signal transconductance } g_m = \frac{2I_D}{(V_{GS} - V_T)} = \sqrt{2\mu_n C_{ox} \left(\frac{W}{L} \right) I_D}$$

Unit conversion:

$$1 \mu\text{m} = 10^{-4} \text{ cm} = 10^{-6} \text{ m}; 1 \text{ nm} = 10^{-7} \text{ cm} = 10^{-9} \text{ m}; 1 \text{ pA} = 10^{-12} \text{ A}; 1 \text{ fF} = 10^{-15} \text{ F}$$

PART III

$$\begin{aligned}\sin x &= \pm \cos(x \mp 90^\circ) \\ \cos x &= \pm \sin(x \pm 90^\circ) \\ \sin x &= -\sin(x \pm 180^\circ) \\ \cos x &= -\cos(x \pm 180^\circ) \\ \sin(-x) &= -\sin x \\ \cos(-x) &= \cos x \\ -\tan^{-1}(x) &= \tan^{-1}(-x)\end{aligned}$$

$$\mathbf{z} = x + jy = |\mathbf{z}| e^{j\theta}$$

$$x = \Re(\mathbf{z}) = |\mathbf{z}| \cos \theta$$

$$y = \Im(\mathbf{z}) = |\mathbf{z}| \sin \theta$$

$$\text{Euler's Identity: } e^{j\theta} = \cos \theta + j \sin \theta$$

$$\mathbf{z}_1 = x_1 + jy_1$$

$$\mathbf{z}_2 = x_2 + jy_2$$

$$\mathbf{z}_1 = \mathbf{z}_2 \text{ iff } x_1 = x_2 \text{ and } y_1 = y_2 \quad \mathbf{z}_1 + \mathbf{z}_2 = (x_1 + x_2) + j(y_1 + y_2)$$

$$\mathbf{z}_1 \mathbf{z}_2 = |\mathbf{z}_1| |\mathbf{z}_2| e^{j(\theta_1 + \theta_2)}$$

$$\frac{\mathbf{z}_1}{\mathbf{z}_2} = \frac{|\mathbf{z}_1|}{|\mathbf{z}_2|} e^{j(\theta_1 - \theta_2)}$$